

CLAIMS

1. An electronic device comprising at least a memory core  
formed of an alloy serving as an electronic conductor and an  
electrode provided on each of both ends of the memory core,  
5 wherein

the memory core is formed of an alloy which is a  
supersaturated solid-solution before writing or at the time of  
data recording and in which phase separation takes place during  
temperature increase.

10 2. An electronic device comprising at least a memory core  
formed of an alloy serving as an electronic conductor and an  
electrode provided on each of both ends of the memory core,  
wherein

the memory core is formed of an alloy which is a phase  
15 separated mixture before writing or at the time of data  
recording and in which the formation of a solid-solution takes  
place during temperature increase.

3. An electronic device comprising at least a memory core  
formed of an alloy serving as an electronic conductor and an  
20 electrode provided on each of both ends of the memory core,  
wherein

the memory core is formed of an alloy which is a compound  
before writing or at the time of data recording and which  
includes a component in which phase separation can take place  
25 during temperature increase.

4. An electronic device comprising at least a memory core  
formed of an alloy serving as an electronic conductor and an  
electrode provided on each of both ends of the memory core,

wherein

the memory core is formed of an alloy which is a phase separated mixture before writing or at the time of data recording and in which a compound is generated during  
5 temperature increase.

5. An electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core, wherein

10 the memory core is formed of an alloy which is an amorphous material before writing or at the time of data recording and in which crystallization takes place during temperature increase.

6. An electronic device comprising at least a memory core  
15 formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core, wherein

the memory core is formed of an alloy which is a compound before writing or at the time of data recording and which  
20 includes a component in which a phase transition to another crystal phase having the same composition takes place during temperature increase.

7. An electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an  
25 electrode provided on each of both ends of the memory core, wherein

the memory core is formed of an alloy which is a supersaturated solid-solution or a phase separated mixture

before writing or at the time of data recording and in which spinodal decomposition or the formation of a solid-solution which is the inverse process can take place during temperature increase.

5           8. An electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core, wherein

the memory core is formed of an alloy which is a compound  
10 or a phase separated mixture before writing or at the time of data recording and in which martensitic transformation can take place during temperature increase.

9. An electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an  
15 electrode provided on each of both ends of the memory core, wherein

the memory core is formed of an alloy which is in a crystallographically stable state before writing or at the time of data recording and in which a non-equilibrium state  
20 accompanying with a solid-solid phase transition can be achieved during temperature increase.

10. An electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core,  
25 wherein

the memory core is formed of an alloy which is in a crystallographically metastable state before writing or at the time of data recording and in which a non-equilibrium state

accompanying with a solid-solid phase transition can be achieved during temperature increase.

11. The electronic device according to any one of claims 1 to 10, wherein

5       at least one of the electrodes connected to the memory core is formed of a semiconductor also having a function for detecting junction resistance.

12. The electronic device according to any one of claims 1 to 10, comprising a third electrode directly connected to the  
10 memory core or a third electrode positioned in close proximity of the memory core and insulated from the memory core, the third electrode for detecting a junction resistance, resistance, an electric potential, or an electric capacity.

13. The electronic device according to any one of claims 1 to 12, wherein  
15

an interface between the memory core and the electrode directly connected with the memory core has a chemical potential adjusting layer having a thickness of at least 0.1 monolayers or more.

20       14. The electronic device according to any one of claims 1 to 13, wherein

the composition of the alloy forming the electronic device is caused to be biased by supplying an electric current to the electronic device to thereby write data on the electronic device.

25       15. An integrated electronic device, wherein: a plurality of the electronic devices according to any one of claims 1 to 14 are arranged in rows and columns; the electrode connected to one of both the ends of the memory core serves as a word line; the

electrode selected from among the other electrodes of the memory core and directly provided on the memory core serves as at least a bit line; and writing-reading operation to the electronic device is achieved by selecting a word line and a bit line to  
5 access a certain electronic device of the plurality of electronic devices arranged in rows and columns.

16. An operation method for an electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of  
10 both ends of the memory core,

wherein the memory core is formed of an alloy which is a supersaturated solid-solution before writing or at the time of data recording, and a temperature of the memory core is changed such that the supersaturated solid-solution is phase-separated  
15 at the time of writing.

17. An operation method for an electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core,

20 wherein the memory core is formed of an alloy which is a phase separated mixture before writing or at the time of data recording, and a temperature of the memory core is changed such that the phase separated mixture is allowed to form a solid-solution at the time of writing.

25 18. An operation method for an electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core,

wherein the memory core is formed of an alloy having a component which is a compound before writing or at the time of data recording, and the temperature of the memory core is changed such that the compound is allowed to phase-separate at  
5 the time of writing.

19. An operation method for an electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core,

10 wherein the memory core is formed of an alloy which is a phase separated mixture before writing or at the time of data recording, and the temperature of the memory core is changed such that the phase separated mixture is allowed to generate a compound at the time of writing.

15 20. An operation method for an electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core,

20 wherein the memory core is formed of an alloy which is an amorphous material before writing or at the time of data recording, and the temperature of the memory core is changed such that the amorphous material is allowed to crystallize at the time of writing.

21. An operation method for an electronic device  
25 comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core,

wherein the memory core is formed of an alloy having a

component which is a compound before writing or at the time of data recording, and the temperature of the memory core is changed such that a phase transition of the compound to another crystal phase having the same composition is allowed to take  
5 place at the time of writing.

22. An operation method for an electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core,  
10 wherein the memory core is formed of an alloy which is a supersaturated solid-solution or a phase-separated mixture before writing or at the time of data recording, and the temperature of the memory core is changed such that the supersaturated solid-solution or the phase-separated mixture is  
15 allowed to spinodally-decompose or form a solid-solution which is the inverse process thereof at the time of writing.

23. An operation method for an electronic device comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of  
20 both ends of the memory core,

wherein the memory core is formed of an alloy which is a compound or a phase separated mixture before writing or at the time of data recording, and the temperature of the memory core is changed such that martensitic transformation of the compound  
25 or the phase separated mixture is allowed to take place at the time of writing.

24. An operation method for an electronic device comprising at least a memory core formed of an alloy serving as

an electronic conductor and an electrode provided on each of both ends of the memory core,

wherein the memory core is formed of an alloy which is in a crystallographically stable state before writing or at the  
5 time of data recording, and the temperature of the memory core is changed such that the alloy is allowed to be in a non-equilibrium state accompanying with a solid-solid phase transition at the time of writing.

25. An operation method for an electronic device  
10 comprising at least a memory core formed of an alloy serving as an electronic conductor and an electrode provided on each of both ends of the memory core,

wherein the memory core is formed of an alloy which is in a crystallographically metastable state before writing or at the  
15 time of data recording, and the temperature of the memory core is changed such that the alloy is allowed to be in a non-equilibrium state accompanying with a solid-solid phase transition at the time of writing.

26. The operation method according to any one of claims 16  
20 to 25, wherein

the composition of the alloy forming the electronic device is caused to be biased by supplying an electric current to the electronic device to thereby write data on the electronic device.